

※ 考生請注意：本試題不可使用計算機

1. A diode is made with following doping levels: $N_A = 10^{16} \text{ cm}^{-3}$ and $N_D = 5 \times 10^{15} \text{ cm}^{-3}$. Assume the intrinsic carrier concentration in silicon at 300 K is $1.5 \times 10^{10} \text{ cm}^{-3}$. Determine the hole and electron concentrations on the two sides, respectively. (20%)
2. In a full-wave rectifier experiment, a student wrongly swaps one of the diode as shown in Fig. 1. Point out the wrongly swapped diode (5%) and explain what happens (10%). (15%)

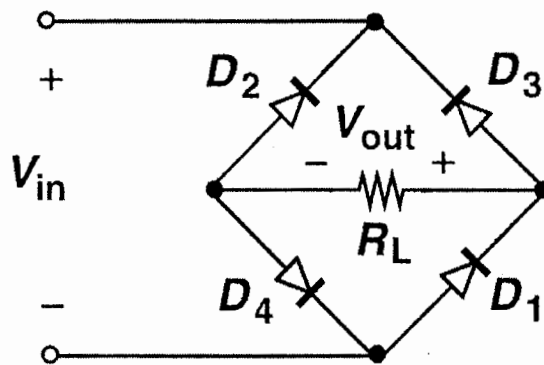


Fig. 1

3. A voltage controlled current source is shown in Fig. 2 with the $K = 20 \text{ mA/V}$. (a) Determine the value of R_L which is necessary to achieve a voltage gain of 15, and (b) If a resistance of R_S is placed in series with the input voltage source, determine V_{out} / V_{in} . (20%)

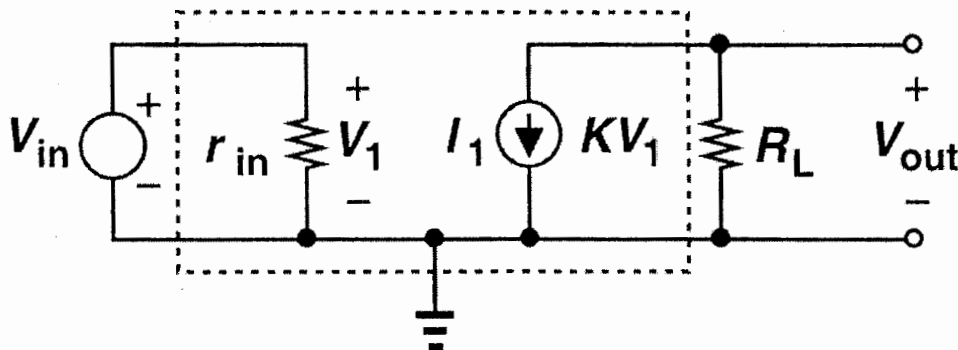


Fig. 2

(背面仍有題目，請繼續作答)

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4. Determine the input and output poles of the circuit as shown in Fig. 3 using Miller's theorem. Assume V_A is infinitely large and neglect other capacitances. (20%)

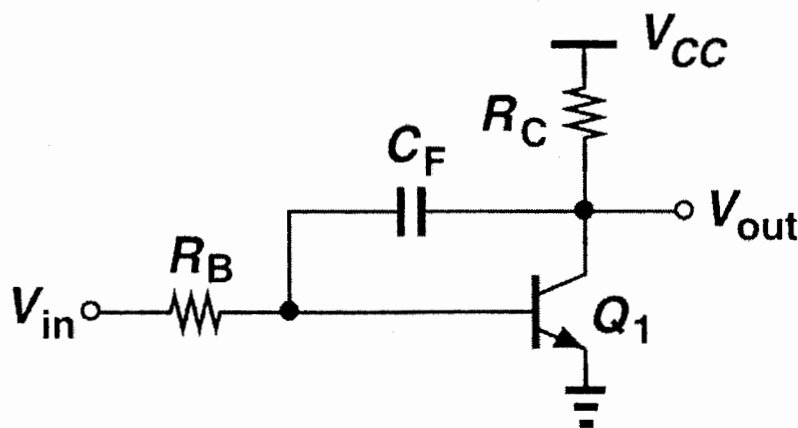


Fig. 3

5. Draw the circuit for an operational amplifier based logarithmic amplifier (5%), and explain with equations (10%). (15%)
6. Describe the concept of virtual ground for ideal operational amplifier. (10%)